

Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

- ... designed for overvoltage protection in crowbar circuits.
- Glass-Passivated Junctions for Greater Parameter Stability and Reliability
- Center-Gate Geometry for Uniform Current Spreading Enabling High Discharge Current
- Small Rugged, Thermowatt or Metal Packages Constructed for Low Thermal Resistance for Maximum Power Dissipation and Durability
- High Capacitor Discharge Current
 - 300 Amps (MCR67, 68)
 - 750 Amps (MCR69)

MAXIMUM RATINGS

Rating	Symbol	Value			Unit
		MCR67	MCR68	MCR69	
Repetitive Peak Forward or Reverse Blocking Voltage, Note 1 ($T_J = -40$ to $+125^\circ\text{C}$)	V_{DRM} or V_{RRM}				Volts
MCR67, 68, 69	-2 -3 -6		50 100 400		
Peak Discharge Current, Note 2	I_{TM}	300	300	750	Amps
On-State Current ($T_C = 85^\circ\text{C}$) (1/2 Cycle, Sine Wave, 60 Hz)	$I_{T(RMS)}$ $I_{T(AV)}$	12 8	12 8	25 16	Amps
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = 125^\circ\text{C}$)	I_{TSM}	100	100	300	Amps
Circuit Fusing ($t = 8.3$ ms)	I^2t	40	40	375	A^2s
Critical Rate-of-Rise of Current (Note 3)	di/dt	75		100	$\text{A}/\mu\text{s}$
Peak Gate Current ($t \leq 2$ μs)	I_{GM}		2		Amps
Peak Gate Power ($t \leq 2$ μs)	P_{GM}		20		Watts
Average Gate Power	$P_{G(AV)}$		0.5		Watt
Operating Junction Temperature Range	T_J	-40 to $+125$			$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$			$^\circ\text{C}$
Mounting Torque	—	15	8	8	in. lb.

THERMAL CHARACTERISTICS

Thermal Resistance, Junction to Case	$R_{\theta JC}$	2	2	1.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$		60		$^\circ\text{C}/\text{W}$

- Notes: 1. V_{DRM} for all types can be applied on a continuous basis over the operating junction temperature range without recurring damage. Ratings apply for open or shorted gate conditions or negative voltage on the gate. Devices should not be tested for blocking voltages such that the supply voltage exceeds the rating of the device.
2. Ratings apply for $t_w = 1$ ms. See Figure 1 for I_{TM} capability for various duration of an exponentially decaying current waveform, t_w is defined as 5 time constants of an exponentially decaying current pulse.
3. Test Conditions: $I_G = 150$ mA, $V_D = \text{Rated } V_{DRM}$, $I_{TM} = \text{Rated Value}$, $T_J = 125^\circ\text{C}$.

**MCR67
Series
MCR68
Series
MCR69
Series**

**SCRs
12 and 25 AMPERES RMS
50 thru 400 VOLTS**



**CASE 221A-04
(TO-220AB)
STYLE 3
MCR68/MCR69 Series**



**CASE 88-01
STYLE 1
MCR67 Series**

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current (Rated V_{DRM} or V_{RRM}) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	I_{DRM} , I_{RRM}	— —	— —	10 2	μA mA
Forward On-State Voltage ($I_{TM} = 24$ Amps), Note 1 MCR67, 68 ($I_{TM} = 50$ Amps), Note 1 MCR69 ($I_{TM} = 300$ Amps, $t_W = 1$ ms), Note 2 MCR67, 68 ($I_{TM} = 750$ Amps, $t_W = 1$ ms), Note 2 MCR69	V_{TM}	— — — —	— — 6 6	2.2 1.8 — —	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12$ V, $R_L = 100 \Omega$)	I_{GT}	2	7	30	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12$ Volts, $R_L = 100 \Omega$) ($V_D = \text{Rated } V_{DRM}$, $R_L = 1$ k Ω , $T_J = 125^\circ\text{C}$)	V_{GT}	— 0.2	0.65 0.40	1.5 —	volts
Holding Current ($I_{TM} = 100$ mA, Gate-Open)	I_H	3	15	50	mA
Latching Current ($V_D = 12$ Vdc, $I_G = 150$ mA, $t_r \leq 50 \mu\text{s}$)	I_L	—	—	60	mA
Critical Rate-of-Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Gate Open, Exponential Waveform, $T_J = 125^\circ\text{C}$)	dv/dt	10	—	—	V/ μs
Gate Controlled Turn-On Time, Note 3 ($V_D = \text{Rated } V_{DRM}$, $I_G = 150$ mA) ($I_{TM} = 24$ Amps, peak) MCR67, 68 ($I_{TM} = 50$ Amps, peak) MCR69	t_{gt}	— —	1 1	— —	μs

Notes: 1. Pulse duration $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.2. Ratings apply for $t_W = 1$ ms. See Figure 1 for I_{TM} capability for various durations of an exponentially decaying current waveform. t_W is defined as 5 time constants of an exponentially decaying current pulse.

3. The gate controlled turn-on time in a crowbar circuit will be influenced by the circuit inductance.

MOTOROLA SC (DIODES/OPTO) 25E D

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FIGURE 1 — PEAK CAPACITOR DISCHARGE CURRENT

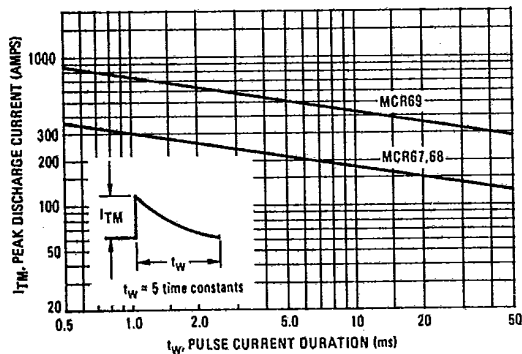
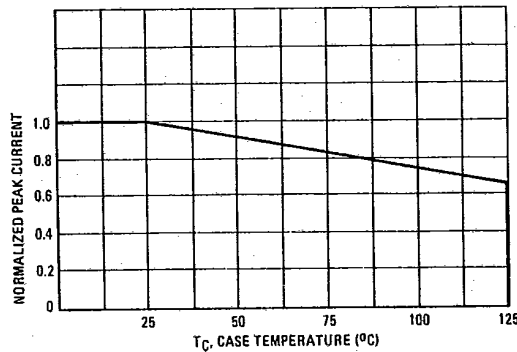


FIGURE 2 — PEAK CAPACITOR DISCHARGE CURRENT DERATING



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FIGURE 3 - CURRENT DERATING
MCR67,68

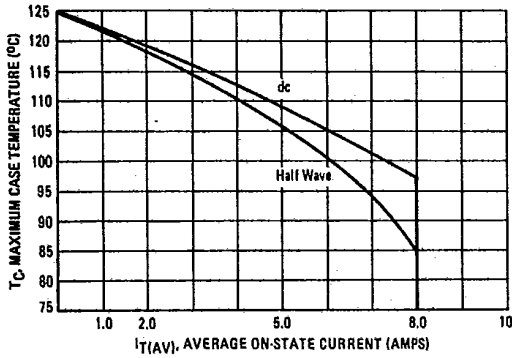
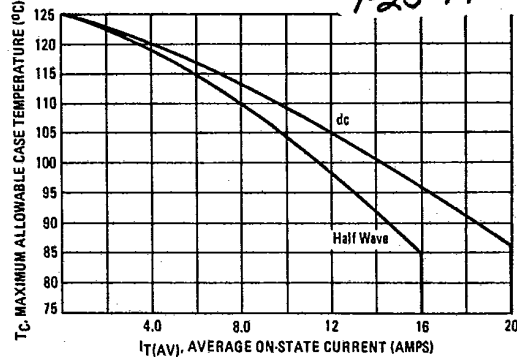


FIGURE 4 - CURRENT DERATING
MCR69



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FIGURE 5 - MAXIMUM POWER DISSIPATION
MCR67,68

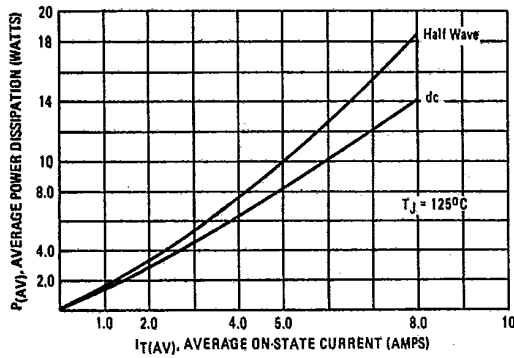


FIGURE 6 - MAXIMUM POWER DISSIPATION
MCR69

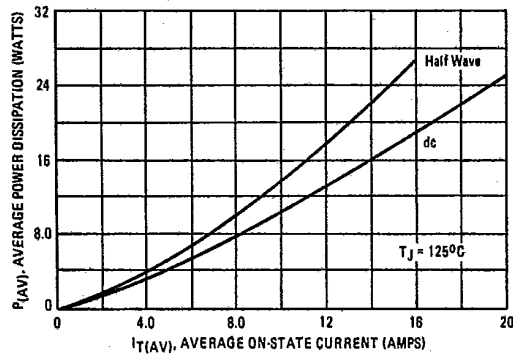
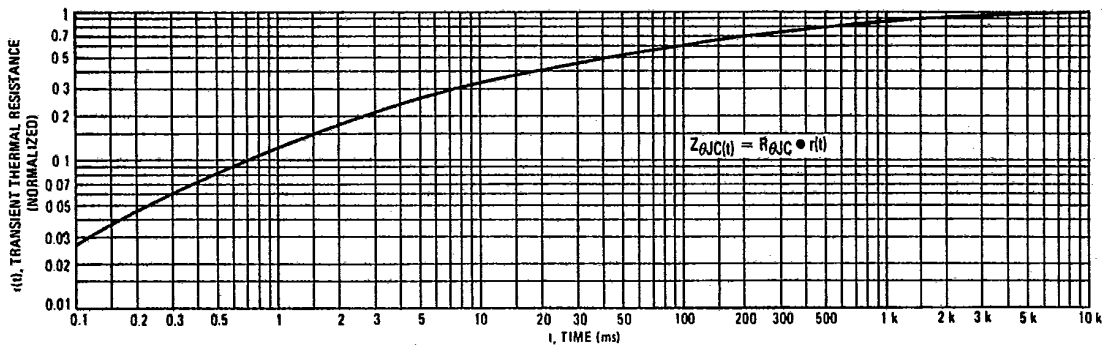


FIGURE 7 - THERMAL RESPONSE



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FIGURE 8 - GATE TRIGGER CURRENT

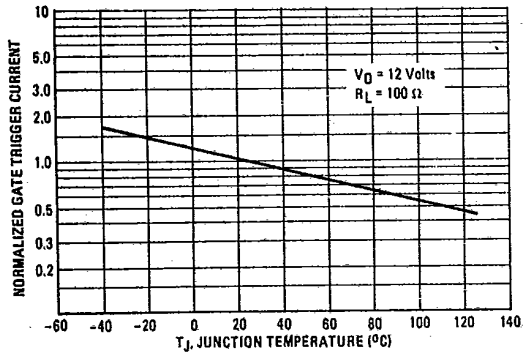
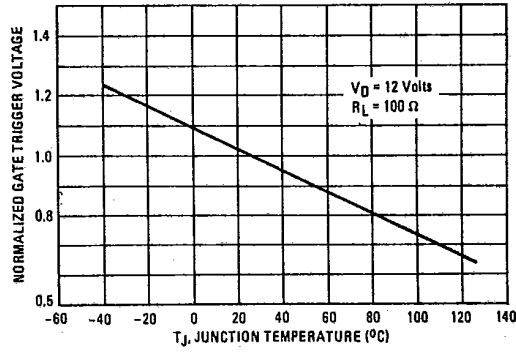


FIGURE 9 - GATE TRIGGER VOLTAGE



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FIGURE 10 - HOLDING CURRENT

